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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/032,563	01/02/2002	Masahiro Ishida	740819-723	5817

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EXAMINER

MALDONADO, JULIO J

ART UNIT	PAPER NUMBER
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2823

DATE MAILED: 03/13/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

10/032,563

Applicant(s)

ISHIDA, MASAHIRO

Examiner

Julio J. Maldonado

Art Unit

2823

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 26 February 2003.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-8 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-8 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on _____ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____.
- 4) ☐ Interview Summary (PTO-413) Paper No(s) _____.
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____.

DETAILED ACTION

1. The final rejection as set forth in paper No.8 is withdrawn in response to applicants' amendments.
2. A new rejection is made as set forth in this Office Action.
3. Claims 1-8 are pending in the application.

Allowable Subject Matter

4. The indicated allowability of claims 3-8 is withdrawn in view of the newly discovered reference(s) to Wang et al. (U.S. 6,113,685). Rejections based on the newly cited reference(s) follow.

Claim Rejections - 35 USC § 103

5. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

6. Claims 1-3 and 5-8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Wang et al. (U.S. 6,113,685) in view of Asai et al. (U.S. 6,426,519 B1).

In reference to claim 1, Wang et al. (Fig.1) in a related method to form a nitride layer teach a first step of forming a raised and a recessed region on an upper portion of a base substrate (12); a second step of growing a semiconductor layer of nitride (10) on said raised and recessed region on said upper portion of said base substrate (12) so that a recessed portion in said raised and recessed region is filled and the upper surface is thereof even; and a third step of irradiating an interface between said

semiconductor layer (10) and said base substrate (12) with a laser beam (14), thereby separating said semiconductor from said base substrate (12) to form a semiconductor substrate from said semiconductor layer (10), wherein in said third step, the laser beam (14) is irradiated upon said semiconductor layer (10) from the surface opposite to the upper portion of said base substrate (12) and upon at least a raised portion in said irregular region while scanning along raised portions surrounded by a groove on said base substrate (12) (column 2, line 20 – column 3, line 25).

Wang et al. fail to teach a first step of selectively forming a raised and recessed region in an upper portion of a base substrate with a plurality of grooves extending parallel to each other, wherein the area occupied by the recessed portions is about in the range from about 1/5 to about 100 times the area occupied by the raised portions. However, Asai et al. (Figs.3-5) in a related method to form a nitride layer teach a first step of selectively forming a raised and recessed region in an upper portion of a base substrate (21) with a plurality of grooves (24) extending parallel to each other, wherein the area occupied by the recessed portions is about the same as the area occupied by the raised portions; and growing a nitride layer (26) over the upper portion of the base substrate (21), wherein forming the raised and recessed regions would result in a nitride layer (26) with reduced dislocations (column 4, line 5 – column 5, line 32). Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the teachings of Asai et al. and Wang et al. to enable the upper surface of Asai to be formed.

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7. Claim 4 is rejected under 35 U.S.C. 103(a) as being unpatentable over Wang et al. ('685) in view of Asai et al. ('519 B1) as applied to claims 1-3 and 5-8 above, and further in view of Sunakawa et al. (U.S. 6,348,096 B1).

The combined teachings of Wang et al. and Asai et al. substantially teach all aspects of the invention including providing a base substrate comprising sapphire but fail to teach wherein the base substrate comprises sapphire whose main surface is in the {0001} plane orientation, and the direction of the zone axis of each said groove is in the {1-100} direction in said base substrate. However, Sunakawa et al. (Fig.1) in a related method to form a nitride layer teach providing a base substrate (11) comprising sapphire whose main surface is in the {0001} plane orientation, and the direction of the zone axis of a plurality of grooves (13) in the {1-100} direction in said base substrate (11) (column 3, line 9 – column 5, line 45). Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to use the sapphire base substrate and the grooves in the plane direction as taught by Sunakawa et al. in the nitride layer formation method as taught by Wang et al. and Asai et al., since this would improve the flatness of the nitride layer (column 5, lines 38 – 45).

Response to Arguments

8. Applicant's arguments with respect to claims 1-8 have been considered but are moot in view of the new ground(s) of rejection.


Conclusion

9. Papers related to this application may be submitted directly to Art Unit 2823 by facsimile transmission. Papers should be faxed to Art Unit 2823 via the Art Unit 2823 Fax Center located in Crystal Plaza 4, room 3C23. The faxing of such papers must conform to the notice published in the Official Gazette, 1096 OG 30 (15 November 1989). The Art Unit 2823 Fax Center number is **(703) 305-3432**. The Art Unit 2823 Fax Center is to be used only for papers related to Art Unit 2823 applications.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to **Julio J. Maldonado** at **(703) 306-0098** and between the hours of 8:00 AM to 4:00 PM (Eastern Standard Time) Monday through Friday or by e-mail via julio.maldonado@uspto.gov. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri, can be reached on (703) 306-2794.

Any inquiry of a general nature or relating to the status of this application should be directed to the **Group 2800 Receptionist** at **(703) 308-0956**.

JMR
3/6/03


George Fourson
Primary Examiner
2823